P-Channel Enhancement Mode Field Effect Transistor

General Description

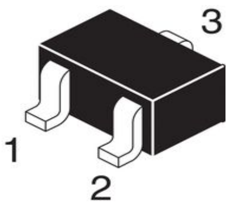
Product Summary		
V_{DSS}	I_D	$R_{DS(ON)}$(mΩ)TYP
-20V	-3.6A	95 @ VGS=-4.5V
		115@ VGS=-2.5V

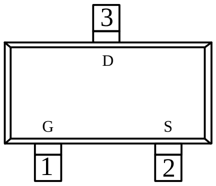
Features

- Super high dense cell design for low $R_{DS(ON)}$
- Rugged and reliable
- Simple drive requirement
- SOT-23-3L/B package

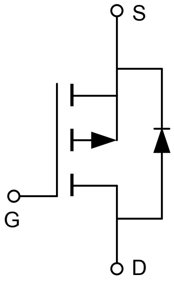
Package

- **SOT-23-3L/B**





SOT-23-3L/B
(Top View)



Ordering Information

Part Number	Storage Temperature	Package	Devices Per Reel
PN2301	-55°C to +150°C	SOT-23-3L/B	3000

Absolute Maximum Ratings

(TA=25℃ unless otherwise noted)

parameter	symbol	limit	unit
Drain-source voltage	V_{DS}	-20	V
Gate-source voltage	V_{GS}	±12	V
Drain current-continuous[a]@Tj=125℃	I_D	-3.6	A
-pulse d[b]	I_{DM}	-11	A
Drain-source Diode forward current	Is	-1.25	A
Maximum power dissipation	P_D	1.25	W
Operating junction Temperature range	Tj	-55—150	℃